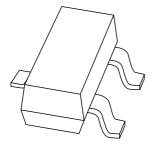
DISCRETE SEMICONDUCTORS

DATA SHEET



PDF.Support

BSR13; **BSR14**NPN switching transistors

Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 13



NPN switching transistors

BSR13; **BSR14**

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

• Switching and linear applications.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complements: BSR15 and BSR16.

MARKING

TYPE NUMBER	MARKING CODE(1)
BSR13	U7*
BSR14	U8*

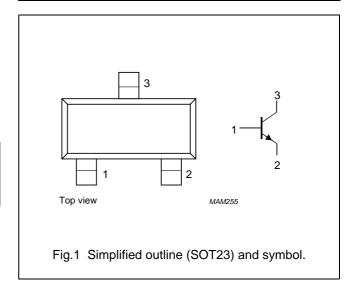
Note

1. * = p: Made in Hong Kong.

* = t : Made in Malaysia. * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE				
NUMBER	NAME	DESCRIPTION	VERSION		
BSR13	_	plastic surface mounted package; 3 leads			
BSR14					

NPN switching transistors

BSR13; BSR14

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BSR13		_	60	V
	BSR14		_	75	V
V _{CEO}	collector-emitter voltage	open base			
	BSR13		_	30	V
	BSR14		_	40	V
V _{EBO}	emitter-base voltage	open collector			
	BSR13		_	5	V
	BSR14		_	6	V
I _C	collector current (DC)		_	800	mA
I _{CM}	peak collector current		_	800	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current				
	BSR13	I _E = 0; V _{CB} = 50 V	_	30	nA
		I _E = 0; V _{CB} = 50 V; T _j = 150 °C	_	10	μΑ
	collector cut-off current				
	BSR14	I _E = 0; V _{CB} = 60 V	_	10	nA
		$I_E = 0$; $V_{CB} = 60 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	10	μΑ
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V			
	BSR13		_	30	nA
	BSR14		_	10	nA

^{1.} Transistor mounted on an FR4 printed-circuit board.

NPN switching transistors

BSR13; BSR14

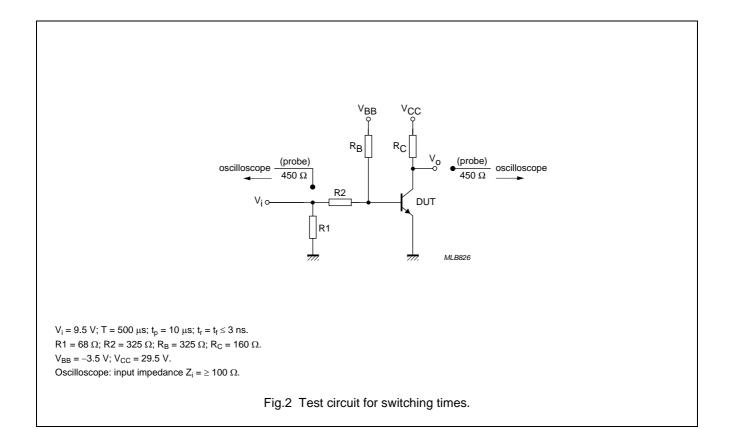
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
h _{FE}	DC current gain	I _C = 0.1 mA; V _{CE} = 10 V; note 1	35	_	
		I _C = 1 mA; V _{CE} = 10 V; note 1	50	_	
		I _C = 10 mA; V _{CE} = 10 V; note 1	75	_	
		I _C = 150 mA; V _{CE} = 10 V; note 1	100	300	
		I _C = 150 mA; V _{CE} = 1 V; note 1	50	_	
	DC current gain	I _C = 500 mA; V _{CE} = 10 V; note 1			
	BSR13		30	_	
	BSR14		40	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA			
	BSR13		_	400	mV
	BSR14		_	300	mV
	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA			
	BSR13		_	1.6	V
	BSR14		_	1	V
V _{BEsat}	base-emitter saturation voltage	I _C = 150 mA; I _B = 15 mA			
	BSR13		_	1.3	V
	BSR14		0.6	1.2	V
	base-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA			
	BSR13		_	2.6	V
	BSR14		_	2	V
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	8	pF
f _T	transition frequency	I _C = 20 mA; V _{CE} = 20 V;			
	BSR13	f = 100 MHz	250	_	MHz
	BSR14		300	_	MHz
Switching t	imes (between 10% and 90% levels); see Fig.2	1	-	
t _{on}	turn-on time	I _{Con} = 150 mA; I _{Bon} = 15 mA;	_	35	ns
t _d	delay time	$I_{Boff} = -15 \text{ mA}$	_	15	ns
t _r	rise time	1	_	20	ns
t _{off}	turn-off time	1	_	250	ns
t _s	storage time	1	_	200	ns
t _f	fall time	1	_	60	ns

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN switching transistors

BSR13; BSR14



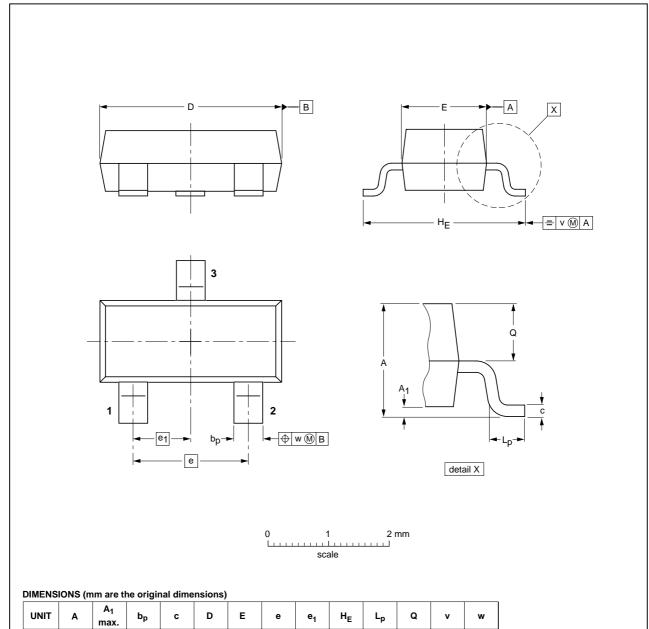
NPN switching transistors

BSR13; BSR14

PACKAGE OUTLINE



SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION ISSUE D	
SOT23		TO-236AB				-04-11-04 06-03-16

1.9

0.45

0.55

0.1

2004 Jan 13 6

0.38

0.9

NPN switching transistors

BSR13; **BSR14**

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

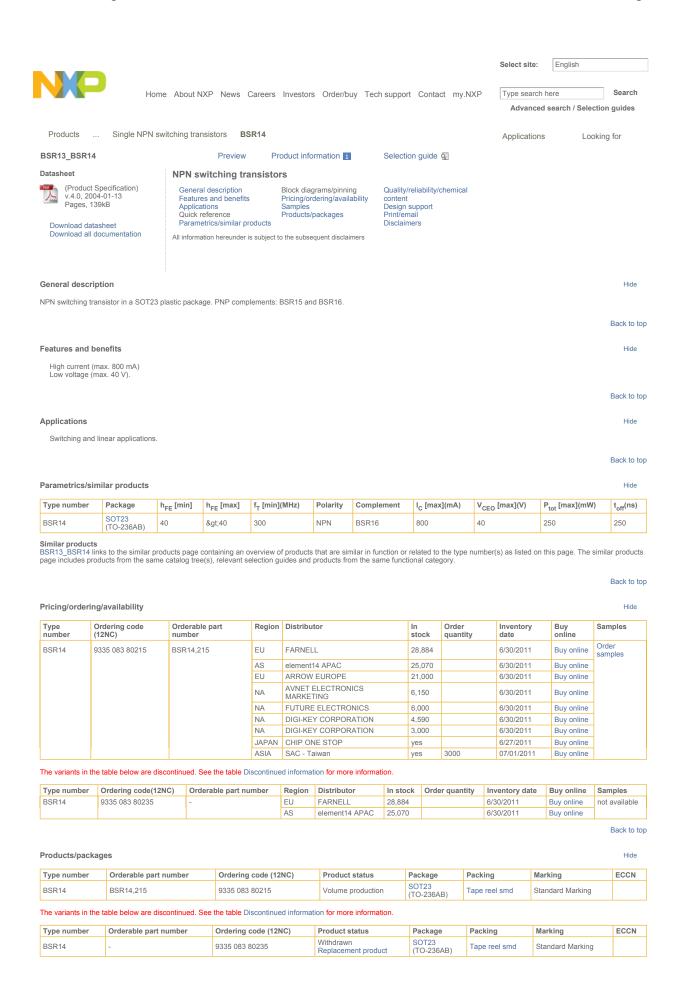
© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands R75/04/pp8 Date of release: 2004 Jan 13 Document order number: 9397 750 12419





Back to top Quality/reliability/chemical content Hide Type number Orderable part number Chemical content RoHS Leadfree conversion date RHF IFR (FIT) MTBF (hours) MSL MSL LF D BSR14 BSR14 week 34, 2003 BSR14.215 EU/CN ROHS COMPLIANT D The variants in the table below are discontinued. See the table Discontinued information for more information. RHF IFR (FIT) MTBF (hours) MSL MSL LF Type number Orderable part number Chemical content RoHS Leadfree conversion date BSR14 BSR14 EU/CN RoHs COMPLIANT D Always Pb-free Quality and reliability disclaimer Back to top Discontinued information Ordering code (12NC) Last-time buy date Last-time delivery date Replacement product DN Notice Status Comments Multi source product Type number fully withdrawn Standard availability Standard End of Life. Inactive part. See 933508380235 PMBT2907A BSR14 31-dec-04 30-jun-05 DN 53 Hide Design support Other type Letter Symbols - Transistors; General (v.1.0, 1999-05-07) Support Models
Spice model of BSR14 Back to top Print/email Hide Email this product information Print this product information Back to top Disclaimers Hide General product disclaimer Quality and reliability disclaimer

NXP | Privacy policy | Terms of use | Sitemap | Mobile app | Switch to classic mode ©2006-2011 NXP Semiconductors. All rights reserved. 沪ICP备1020807

http://www.nxp.com/